

Features

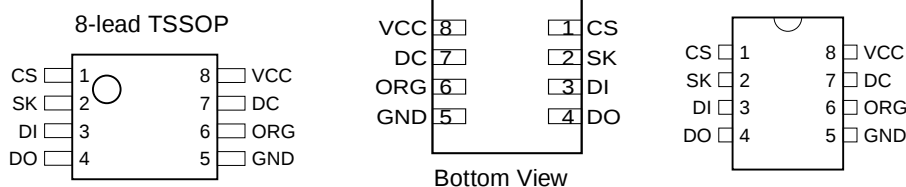
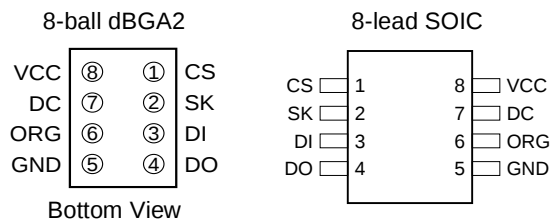
- Low-voltage and Standard-voltage Operation
 - 2.7 ($V_{CC} = 2.7V$ to 5.5V)
 - 1.8 ($V_{CC} = 1.8V$ to 5.5V)
- User-selectable Internal Organization
 - 2K: 256 x 8 or 128 x 16
 - 4K: 512 x 8 or 256 x 16
- 3-wire Serial Interface
- Sequential Read Operation
- 2 MHz Clock Rate (5V)
- Self-timed Write Cycle (10 ms Max)
- High Reliability
 - Endurance: 1 Million Write Cycles
 - Data Retention: 100 Years
- Automotive Grade, Extended Temperature, and Lead-free/Halogen-free Devices Available
- 8-lead PDIP, 8-lead JEDEC SOIC, 8-lead EIAJ SOIC, 8-lead MAP, 8-lead TSSOP, and 8-ball dBGAATM Packages

Description

The AT93C56A/66A provides 2048/4096 bits of serial electrically erasable program-mable read-only memory (EEPROM) organized as 128/256 words of 16 bits each when the ORG pin is connected to VCC and 256/512 words of 8 bits each when it is tied to ground. The device is optimized for use in many industrial and commercial applications where low-power and low-voltage operations are essential. The AT93C56A/66A is available in space-saving 8-lead PDIP, 8-lead JEDEC SOIC, 8-lead EIAJ SOIC, 8-lead MAP, 8-lead TSSOP, and 8-ball dBGAATM packages.

Pin Configurations

Pin Name	Function
CS	Chip Select
SK	Serial Data Clock
DI	Serial Data Input
DO	Serial Data Output
GND	Ground
VCC	Power Supply
ORG	Internal Organization
DC	Don't Connect



3-wire Serial EEPROMs

2K (256 x 8 or 128 x 16)

4K (512 x 8 or 256 x 16)

AT93C56A AT93C66A

Advance Information

Rev. 3378F-SEEPR-04/04



The AT93C56A/66A is enabled through the Chip Select pin (CS) and accessed via a 3-wire serial interface consisting of Data Input (DI), Data Output (DO), and Shift Clock (SK). Upon receiving a READ instruction at DI, the address is decoded and the data is clocked out serially on the data output pin DO. The WRITE cycle is completely self-timed and no separate ERASE cycle is required before WRITE. The WRITE cycle is only enabled when the part is in the ERASE/WRITE ENABLE state. When CS is brought "high" following the initiation of a WRITE cycle, the DO pin outputs the READY/BUSY status of the part.

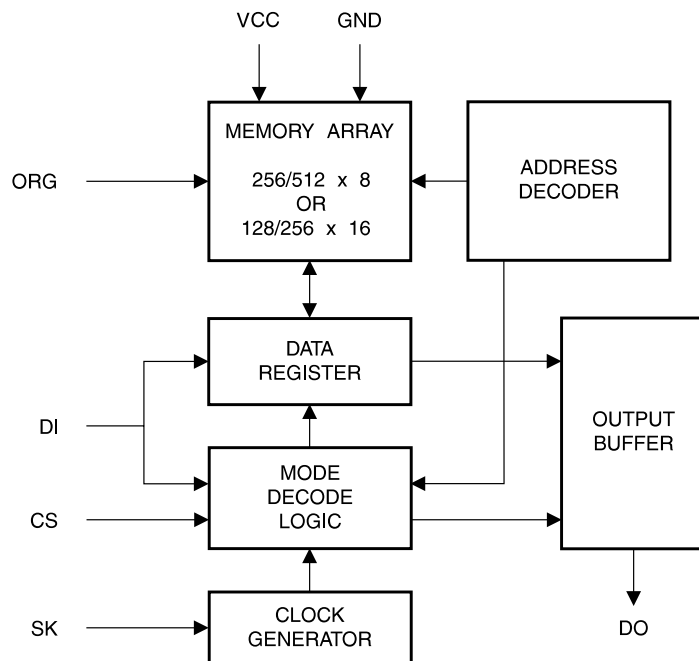
The AT93C56A/66A is available in 2.7V to 5.5V and 1.8V to 5.5V versions.

Absolute Maximum Ratings*

Operating Temperature.....	-55°C to +125°C
Storage Temperature	-65°C to +150°C
Voltage on Any Pin with Respect to Ground.....	-1.0V to +7.0V
Maximum Operating Voltage	6.25V
DC Output Current.....	5.0 mA

***NOTICE:** Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability

Block Diagram



Note: When the ORG pin is connected to VCC, the x 16 organization is selected. When it is connected to ground, the x 8 organization is selected. If the ORG pin is left unconnected and the application does not load the input beyond the capability of the internal 1 Meg ohm pullup, then the x 16 organization is selected. The feature is not available on the 1.8V devices.

Pin Capacitance⁽¹⁾

Applicable over recommended operating range from $T_A = 25^\circ\text{C}$, $f = 1.0\text{ MHz}$, $V_{CC} = +5.0\text{V}$ (unless otherwise noted).

Symbol	Test Conditions	Max	Units	Conditions
C_{OUT}	Output Capacitance (DO)	5	pF	$V_{OUT} = 0\text{V}$
C_{IN}	Input Capacitance (CS, SK, DI)	5	pF	$V_{IN} = 0\text{V}$

Note: 1. This parameter is characterized and is not 100% tested.

DC Characteristics

Applicable over recommended operating range from: $T_{AI} = -40^\circ\text{C}$ to $+85^\circ\text{C}$, $V_{CC} = +1.8\text{V}$ to $+5.5\text{V}$,

$T_{AE} = -40^\circ\text{C}$ to $+125^\circ\text{C}$, $V_{CC} = +1.8\text{V}$ to $+5.5\text{V}$ (unless otherwise noted).

Symbol	Parameter	Test Condition		Min	Typ	Max	Unit
V_{CC1}	Supply Voltage			1.8		5.5	V
V_{CC2}	Supply Voltage			2.7		5.5	V
V_{CC3}	Supply Voltage			4.5		5.5	V
I_{CC}	Supply Current	$V_{CC} = 5.0\text{V}$	READ at 1.0 MHz		0.5	2.0	mA
			WRITE at 1.0 MHz		0.5	2.0	mA
I_{SB1}	Standby Current	$V_{CC} = 1.8\text{V}$	CS = 0V		0	0.1	μA
I_{SB2}	Standby Current	$V_{CC} = 2.7\text{V}$	CS = 0V		6.0	10.0	μA
I_{SB3}	Standby Current	$V_{CC} = 5.0\text{V}$	CS = 0V		17	30	μA
I_{IL}	Input Leakage	$V_{IN} = 0\text{V}$ to V_{CC}			0.1	3.0	μA
I_{OL}	Output Leakage	$V_{IN} = 0\text{V}$ to V_{CC}			0.1	3.0	μA
$V_{IL1}^{(1)}$ $V_{IH1}^{(1)}$	Input Low Voltage Input High Voltage	$2.7\text{V} \leq V_{CC} \leq 5.5\text{V}$		-0.6 2.0		0.8 $V_{CC} + 1$	V
$V_{IL2}^{(1)}$ $V_{IH2}^{(1)}$	Input Low Voltage Input High Voltage	$1.8\text{V} \leq V_{CC} \leq 2.7\text{V}$		-0.6 $V_{CC} \times 0.7$		$V_{CC} \times 0.3$ $V_{CC} + 1$	V
V_{OL1} V_{OH1}	Output Low Voltage Output High Voltage	$2.7\text{V} \leq V_{CC} \leq 5.5\text{V}$	$I_{OL} = 2.1\text{ mA}$			0.4	V
			$I_{OH} = -0.4\text{ mA}$	2.4			V
V_{OL2} V_{OH2}	Output Low Voltage Output High Voltage	$1.8\text{V} \leq V_{CC} \leq 2.7\text{V}$	$I_{OL} = 0.15\text{ mA}$			0.2	V
			$I_{OH} = -100\text{ }\mu\text{A}$	$V_{CC} - 0.2$			V

Note: 1. V_{IL} min and V_{IH} max are reference only and are not tested.

AC Characteristics

Applicable over recommended operating range from $T_{AI} = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$, $T_{AE} = -40^{\circ}\text{C}$ to $+125^{\circ}\text{C}$, $V_{CC} = \text{As Specified}$, $CL = 1$ TTL Gate and 100 pF (unless otherwise noted).

Symbol	Parameter	Test Condition		Min	Typ	Max	Units
f_{SK}	SK Clock Frequency	$4.5V \leq V_{CC} \leq 5.5V$ $2.7V \leq V_{CC} \leq 5.5V$ $1.8V \leq V_{CC} \leq 5.5V$		0 0 0		2 1 0.25	MHz
t_{SKH}	SK High Time	$2.7V \leq V_{CC} \leq 5.5V$ $1.8V \leq V_{CC} \leq 5.5V$		250 1000			ns
t_{SKL}	SK Low Time	$2.7V \leq V_{CC} \leq 5.5V$ $1.8V \leq V_{CC} \leq 5.5V$		250 1000			ns
t_{CS}	Minimum CS Low Time	$2.7V \leq V_{CC} \leq 5.5V$ $1.8V \leq V_{CC} \leq 5.5V$		250 1000			ns
t_{CSS}	CS Setup Time	Relative to SK	$2.7V \leq V_{CC} \leq 5.5V$ $1.8V \leq V_{CC} \leq 5.5V$	50 200			ns
t_{DIS}	DI Setup Time	Relative to SK	$2.7V \leq V_{CC} \leq 5.5V$ $1.8V \leq V_{CC} \leq 5.5V$	100 400			ns
t_{CSH}	CS Hold Time	Relative to SK		0			ns
t_{DIH}	DI Hold Time	Relative to SK	$2.7V \leq V_{CC} \leq 5.5V$ $1.8V \leq V_{CC} \leq 5.5V$	100 400			ns
t_{PD1}	Output Delay to "1"	AC Test	$2.7V \leq V_{CC} \leq 5.5V$ $1.8V \leq V_{CC} \leq 5.5V$			250 1000	ns
t_{PD0}	Output Delay to "0"	AC Test	$2.7V \leq V_{CC} \leq 5.5V$ $1.8V \leq V_{CC} \leq 5.5V$			250 1000	ns
t_{SV}	CS to Status Valid	AC Test	$2.7V \leq V_{CC} \leq 5.5V$ $1.8V \leq V_{CC} \leq 5.5V$			250 1000	ns
t_{DF}	CS to DO in High Impedance	AC Test CS = V_{IL}	$2.7V \leq V_{CC} \leq 5.5V$ $1.8V \leq V_{CC} \leq 5.5V$			150 400	ns
t_{WP}	Write Cycle Time					10	ms
			$4.5V \leq V_{CC} \leq 5.5V$	0.1	3		ms
Endurance ⁽¹⁾	5.0V, 25°C, Page Mode			1M			Write Cycles

Note: 1. This parameter is characterized and is not 100% tested.

Instruction Set for the AT93C56A and AT93C66A

Instruction	SB	Op Code	Address		Data		Comments
			x 8	x 16	x 8	x 16	
READ	1	10	$A_8 - A_0$	$A_7 - A_0$			Reads data stored in memory, at specified address.
EWEN	1	00	11XXXXXXXX	11XXXXXXXX			Write enable must precede all programming modes.
ERASE	1	11	$A_8 - A_0$	$A_7 - A_0$			Erases memory location $A_n - A_0$.
WRITE	1	01	$A_8 - A_0$	$A_7 - A_0$	$D_7 - D_0$	$D_{15} - D_0$	Writes memory location $A_n - A_0$.
ERAL	1	00	10XXXXXXXX	10XXXXXXXX			Erases all memory locations. Valid only at $V_{CC} = 4.5V$ to $5.5V$.
WRAL	1	00	01XXXXXXXX	01XXXXXXXX	$D_7 - D_0$	$D_{15} - D_0$	Writes all memory locations. Valid only at $V_{CC} = 5.0V \pm 10\%$ and Disable Register cleared.
EWDS	1	00	00XXXXXXXX	00XXXXXXXX			Disables all programming instructions.

Note: The X's in the address field represent don't care values and must be clocked.

Functional Description

The AT93C56A/66A is accessed via a simple and versatile 3-wire serial communication interface. Device operation is controlled by seven instructions issued by the host processor. **A valid instruction starts with a rising edge of CS** and consists of a Start Bit (logic "1") followed by the appropriate Op Code and the desired memory address location.

READ (READ): The Read (READ) instruction contains the address code for the memory location to be read. After the instruction and address are decoded, data from the selected memory location is available at the serial output pin DO. Output data changes are synchronized with the rising edges of serial clock SK. It should be noted that a dummy bit (logic "0") precedes the 8- or 16-bit data output string. The AT93C56A/66A supports sequential read operations. The device will automatically increment the internal address pointer and clock out the next memory location as long as Chip Select (CS) is held high. In this case, the dummy bit (logic "0") will not be clocked out between memory locations, thus allowing for a continuous stream of data to be read.

ERASE/WRITE (EWEN): To assure data integrity, the part automatically goes into the Erase/Write Disable (EWDS) state when power is first applied. An Erase/Write Enable (EWEN) instruction must be executed first before any programming instructions can be carried out. Please note that once in the EWEN state, programming remains enabled until an EWDS instruction is executed or V_{CC} power is removed from the part.

ERASE (ERASE): The Erase (ERASE) instruction programs all bits in the specified memory location to the logical "1" state. The self-timed erase cycle starts once the ERASE instruction and address are decoded. The DO pin outputs the READY/BUSY status of the part if CS is brought high after being kept low for a minimum of 250 ns (t_{CS}). A logic "1" at pin DO indicates that the selected memory location has been erased, and the part is ready for another instruction.

WRITE (WRITE): The Write (WRITE) instruction contains the 8 or 16 bits of data to be written into the specified memory location. The self-timed programming cycle t_{WP} starts after the last bit of data is received at serial data input pin DI. The DO pin outputs the READY/BUSY status of the part if CS is brought high after being kept low for a minimum of 250 ns (t_{CS}). A logic “0” at DO indicates that programming is still in progress. A logic “1” indicates that the memory location at the specified address has been written with the data pattern contained in the instruction and the part is ready for further instructions. **A READY/BUSY status cannot be obtained if the CS is brought high after the end of the self-timed programming cycle t_{WP} .**

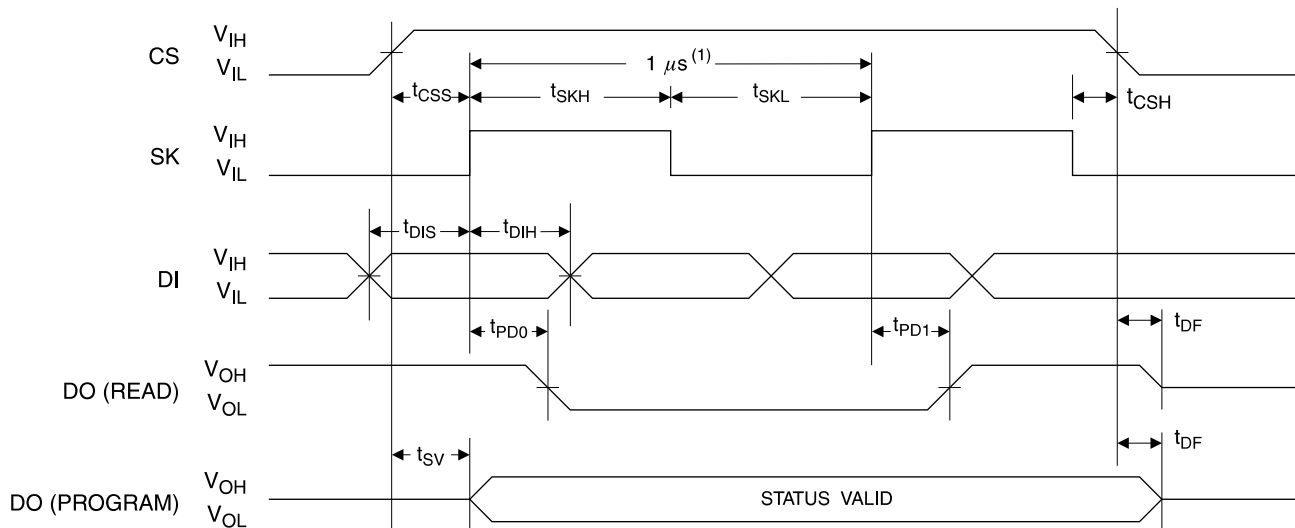
ERASE ALL (ERAL): The Erase All (ERAL) instruction programs every bit in the memory array to the logic “1” state and is primarily used for testing purposes. The DO pin outputs the READY/BUSY status of the part if CS is brought high after being kept low for a minimum of 250 ns (t_{CS}). The ERAL instruction is valid only at $V_{CC} = 5.0V \pm 10\%$.

WRITE ALL (WRAL): The Write All (WRAL) instruction programs all memory locations with the data patterns specified in the instruction. The DO pin outputs the READY/BUSY status of the part if CS is brought high after being kept low for a minimum of 250 ns (t_{CS}). The WRAL instruction is valid only at $V_{CC} = 5.0V \pm 10\%$.

ERASE/WRITE DISABLE (EWDS): To protect against accidental data disturb, the Erase/Write Disable (EWDS) instruction disables all programming modes and should be executed after all programming operations. The operation of the READ instruction is independent of both the EWEN and EWDS instructions and can be executed at any time.

Timing Diagrams

Synchronous Data Timing



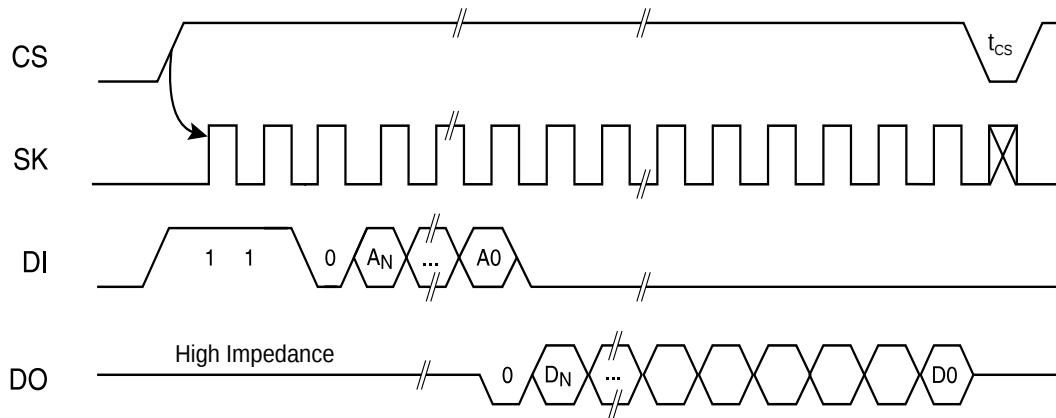
Note: 1. This is the minimum SK period.

Organization Key for Timing Diagrams

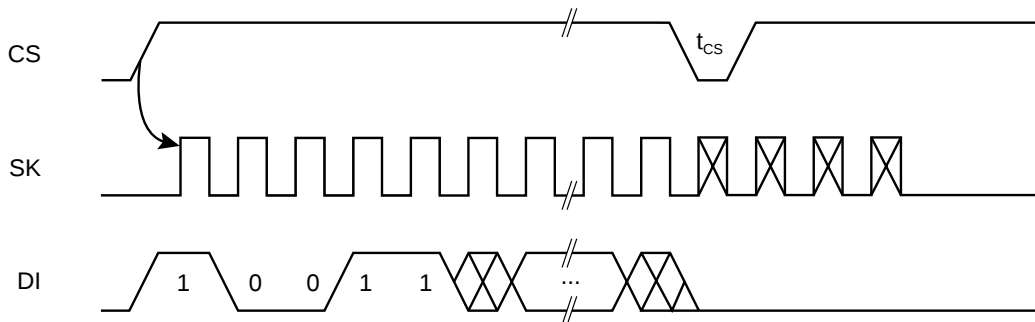
I/O	AT93C56A (2K)		AT93C66A (4K)	
	x 8	x 16	x 8	x 16
A_N	$A_8^{(1)}$	$A_7^{(2)}$	A_8	A_7
D_N	D_7	D_{15}	D_7	D_{15}

Notes: 1. A_8 is a DON'T CARE value, but the extra clock is required.
 2. A_7 is a DON'T CARE value, but the extra clock is required.

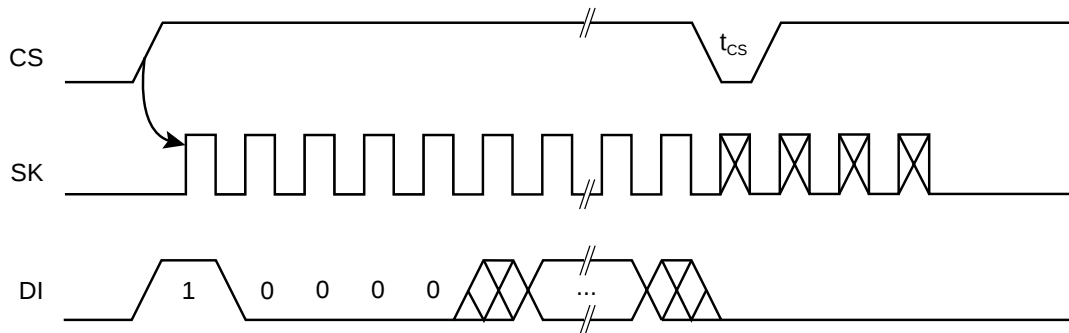
READ Timing



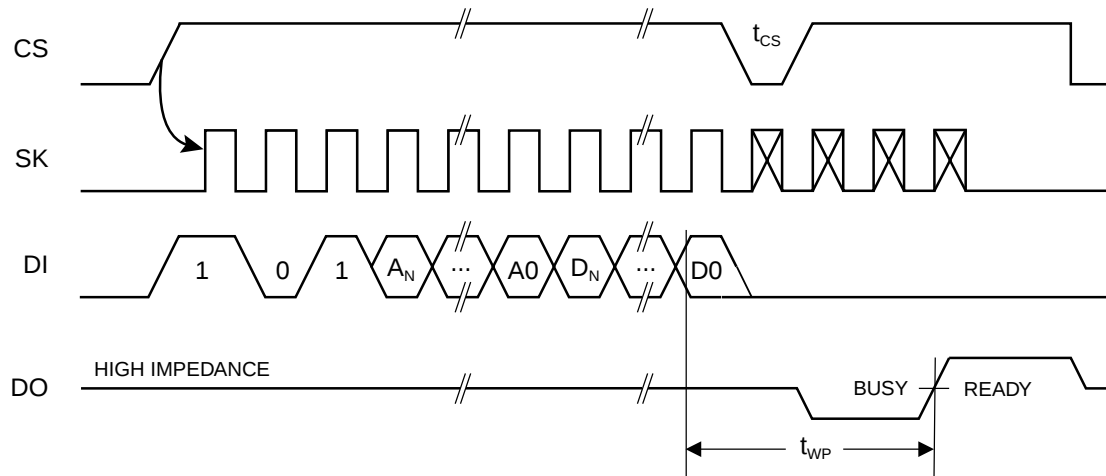
EWEN Timing



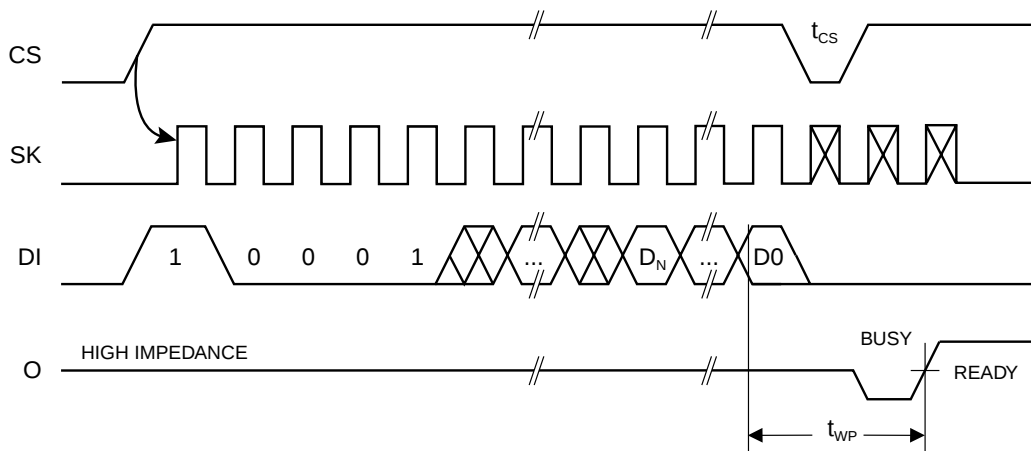
EWDS Timing



WRITE Timing

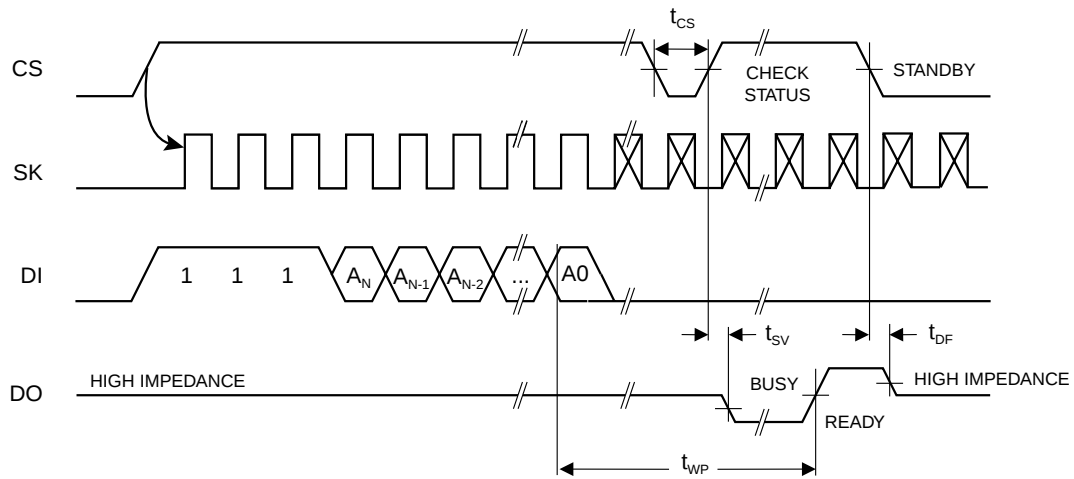


WRAL Timing⁽¹⁾

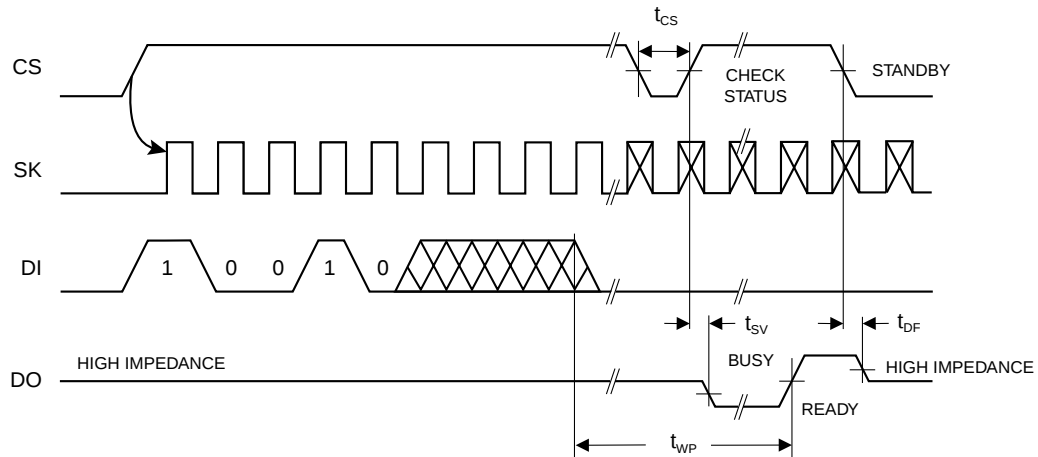


Note: 1. Valid only at $V_{CC} = 4.5V$ to $5.5V$.

ERASE Timing



ERASE Timing⁽¹⁾



Note: 1. Valid only at $V_{CC} = 4.5V$ to $5.5V$.

AT93C56A Ordering Information

Ordering Code	Package	Operation Range
AT93C56A-10PI-2.7	8P3	Industrial Temperature (–40°C to 85°C)
AT93C56A-10SI-2.7	8S1	
AT93C56AW-10SI-2.7	8S2	
AT93C56A-10TI-2.7	8A2	
AT93C56AU3-10UI-2.7	8U3-1	
AT93C56AY1-10YI-2.7	8Y1	
AT93C56A-10PI-1.8	8P3	Industrial Temperature (–40°C to 85°C)
AT93C56A-10SI-1.8	8S1	
AT93C56AW-10SI-1.8	8S2	
AT93C56A-10TI-1.8	8A2	
AT93C56AU3-10UI-1.8	8U3-1	
AT93C56AY1-10YI-1.8	8Y1	
AT93C56A-10SU-2.7	8S1	Lead-free/Halogen-free/ Industrial Temperature (–40°C to 85°C)
AT93C56A-10SU-1.8	8S1	
AT93C56A-10TU-2.7	8A2	
AT93C56A-10TU-1.8	8A2	
AT93C56A-10SQ-2.7	8S1	Lead-free/Halogen-free/ High Grade/Extended Temperature (–40°C to 125°C)
AT93C56A-10SE-2.7	8S1	High Grade/Extended Temperature (–40°C to 125°C)

Note: For 2.7V devices used in the 4.5V to 5.5V range, please refer to performance values in the AC and DC characteristics table.

Package Type	
8P3	8-lead, 0.300" Wide, Plastic Dual Inline Package (PDIP)
8S1	8-lead, 0.150" Wide, Plastic Gull Wing Small Outline (JEDEC SOIC)
8S2	8-lead, 0.200" Wide, Plastic Gull Wing Small Outline (EIAJ SOIC)
8A2	8-lead, 0.170" Wide, Thin Shrink Small Outline Package (TSSOP)
8U3-1	8-ball, die Ball Grid Array Package (dBGAA2)
8Y1	8-lead, 4.90 mm x 3.00 mm Body, Dual Footprint, Non-leaded, Miniature Array Package (MAP)
Options	
–2.7	Low-voltage (2.7V to 5.5V)
1.8	Low-voltage (1.8V to 5.5V)

AT93C66A Ordering Information

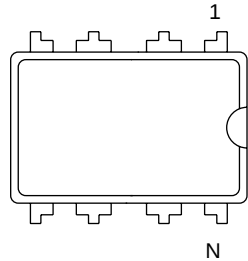
Ordering Code	Package	Operation Range
AT93C66A-10PI-2.7 AT93C66A-10SI-2.7 AT93C66AW-10SI-2.7 AT93C66A-10TI-2.7 AT93C66AU3-10UI-2.7 AT93C66AY1-10YI-2.7	8P3 8S1 8S2 8A2 8U3-1 8Y1	Industrial (–40°C to 85°C)
AT93C66A-10PI-1.8 AT93C66A-10SI-1.8 AT93C66AW-10SI-1.8 AT93C66A-10TI-1.8 AT93C66AU3-10UI-1.8 AT93C66AY1-10YI-1.8	8P3 8S1 8S2 8A2 8U3-1 8Y1	Industrial (–40°C to 85°C)
AT93C66A-10SU-2.7 AT93C66A-10SU-1.8 AT93C66A-10TU-2.7 AT93C66A-10TU-1.8	8S1 8S1 8A2 8A2	Lead-free/Halogen-free/ Industrial Temperature (–40°C to 85°C)
AT93C66A-10SQ-2.7	8S1	Lead-free/Halogen-free/ High Grade/Extended Temperature (–40°C to 125°C)
AT93C66A-10SE-2.7	8S1	High Grade/Extended Temperature (–40°C to 125°C)

Note: For 2.7V devices used in the 4.5V to 5.5V range, please refer to performance values in the AC and DC characteristics table.

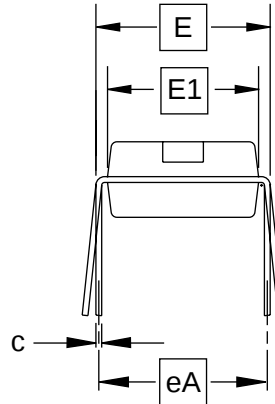
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Options	
–2.7	Low-voltage (2.7V to 5.5V)
–1.8	Low-voltage (1.8V to 5.5V)

Packaging Information

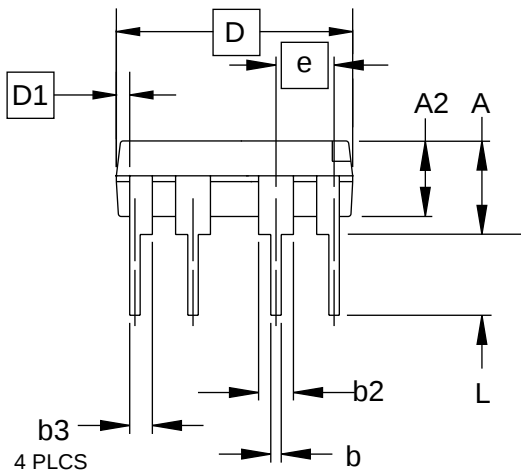
8P3 – PDIP



Top View



End View



Side View

COMMON DIMENSIONS
(Unit of Measure = inches)

SYMBOL	MIN	NOM	MAX	NOTE
A			0.210	2
A2	0.115	0.130	0.195	
b	0.014	0.018	0.022	5
b2	0.045	0.060	0.070	6
b3	0.030	0.039	0.045	6
c	0.008	0.010	0.014	
D	0.355	0.365	0.400	3
D1	0.005			3
E	0.300	0.310	0.325	4
E1	0.240	0.250	0.280	3
e	0.100 BSC			
eA	0.300 BSC			4
L	0.115	0.130	0.150	2

- Notes:
1. This drawing is for general information only; refer to JEDEC Drawing MS-001, Variation BA for additional information.
 2. Dimensions A and L are measured with the package seated in JEDEC seating plane Gauge GS-3.
 3. D, D1 and E1 dimensions do not include mold Flash or protrusions. Mold Flash or protrusions shall not exceed 0.010 inch.
 4. E and eA measured with the leads constrained to be perpendicular to datum.
 5. Pointed or rounded lead tips are preferred to ease insertion.
 6. b2 and b3 maximum dimensions do not include Dambar protrusions. Dambar protrusions shall not exceed 0.010 (0.25 mm).

01/09/02



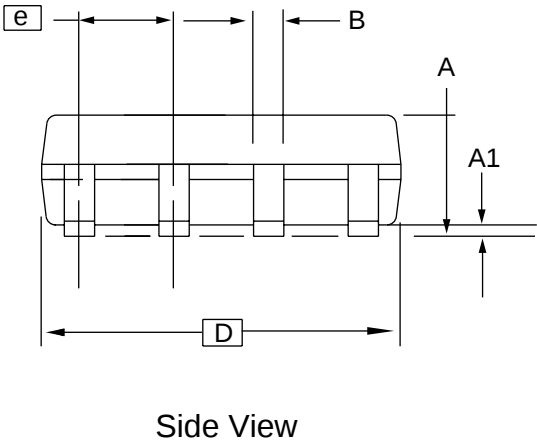
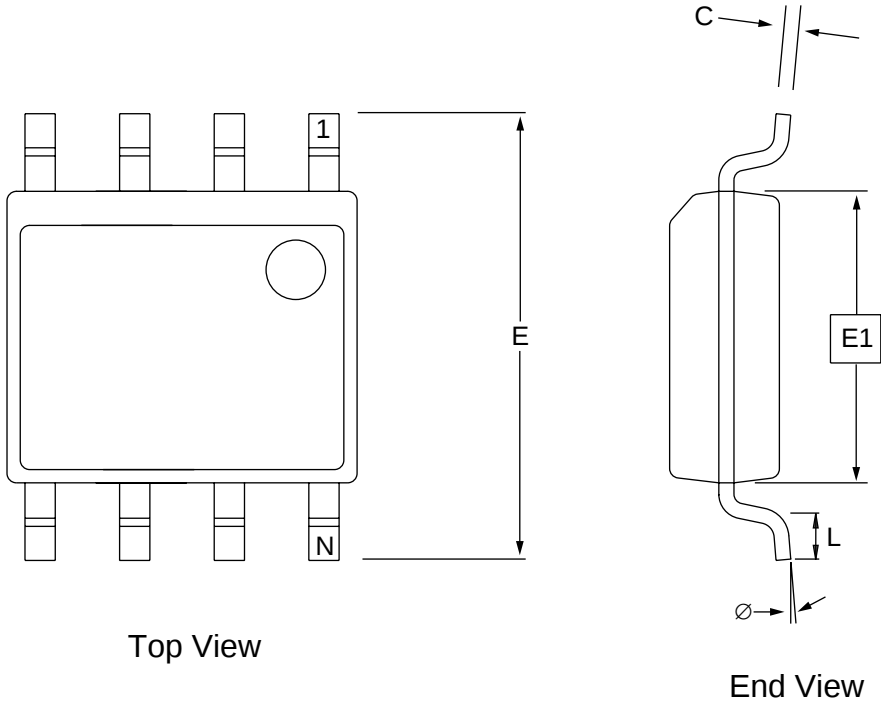
2325 Orchard Parkway
San Jose, CA 95131

TITLE
8P3, 8-lead, 0.300" Wide Body, Plastic Dual
In-line Package (PDIP)

DRAWING NO.
8P3

REV.
B

8S1 – JEDEC SOIC



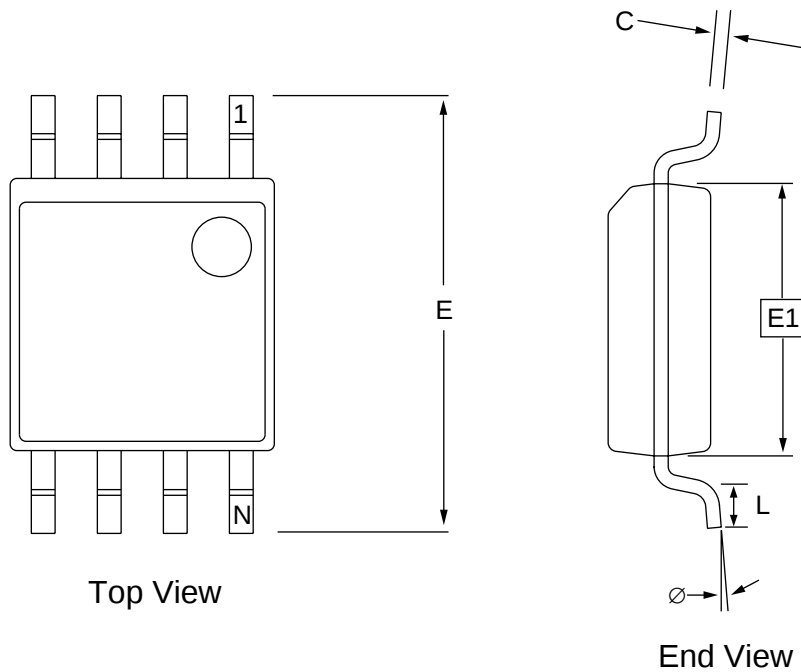
COMMON DIMENSIONS				
(Unit of Measure = mm)				
SYMBOL	MIN	NOM	MAX	NOTE
A	1.35	–	1.75	
A1	0.10	–	0.25	
b	0.31	–	0.51	
C	0.17	–	0.25	
D	4.80	–	5.00	
E1	3.81	–	3.99	
E	5.79	–	6.20	
e	1.27 BSC			
L	0.40	–	1.27	
Ø	0°	–	8°	

Note: These drawings are for general information only. Refer to JEDEC Drawing MS-012, Variation AA for proper dimensions, tolerances, datums, etc.

10/7/03

	1150 E. Cheyenne Mtn. Blvd. Colorado Springs, CO 80906	TITLE 8S1, 8-lead (0.150" Wide Body), Plastic Gull Wing Small Outline (JEDEC SOIC)	DRAWING NO. 8S1	REV. B

8S2 – EIAJ SOIC



COMMON DIMENSIONS
(Unit of Measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
A	1.70		2.16	
A1	0.05		0.25	
b	0.35		0.48	5
C	0.15		0.35	5
D	5.13		5.35	
E1	5.18		5.40	2, 3
E	7.70		8.26	
L	0.51		0.85	
Ø	0°		8°	
e	1.27 BSC			4

- Notes: 1. This drawing is for general information only; refer to EIAJ Drawing EDR-7320 for additional information.
 2. Mismatch of the upper and lower dies and resin burrs are not included.
 3. It is recommended that upper and lower cavities be equal. If they are different, the larger dimension shall be regarded.
 4. Determines the true geometric position.
 5. Values b and C apply to pb/Sn solder plated terminal. The standard thickness of the solder layer shall be 0.010 +0.010/-0.005 mm.

10/7/03



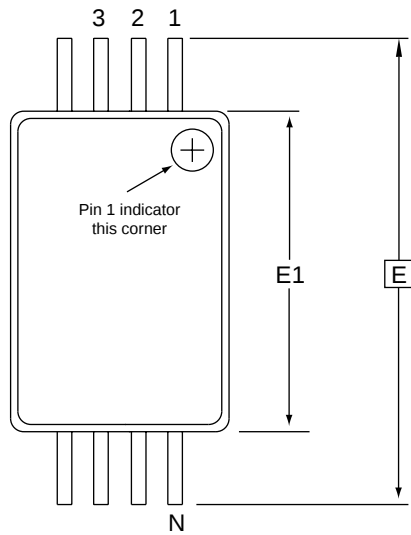
2325 Orchard Parkway
San Jose, CA 95131

TITLE
8S2, 8-lead, 0.209" Body, Plastic Small
Outline Package (EIAJ)

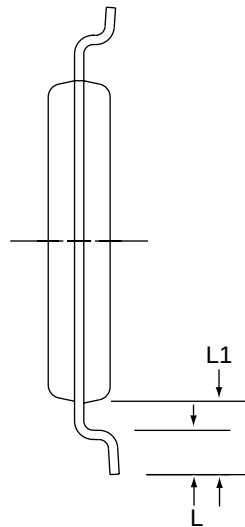
DRAWING NO.
8S2

REV.
C

8A2 – TSSOP



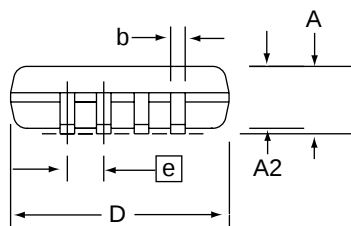
Top View



End View

COMMON DIMENSIONS (Unit of Measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
D	2.90	3.00	3.10	2, 5
E	6.40 BSC			
E1	4.30	4.40	4.50	3, 5
A	–	–	1.20	
A2	0.80	1.00	1.05	
b	0.19	–	0.30	4
e	0.65 BSC			
L	0.45	0.60	0.75	
L1	1.00 REF			



Side View

- Notes:
1. This drawing is for general information only. Refer to JEDEC Drawing MO-153, Variation AA, for proper dimensions, tolerances, datums, etc.
 2. Dimension D does not include mold Flash, protrusions or gate burrs. Mold Flash, protrusions and gate burrs shall not exceed 0.15 mm (0.006 in) per side.
 3. Dimension E1 does not include inter-lead Flash or protrusions. Inter-lead Flash and protrusions shall not exceed 0.25 mm (0.010 in) per side.
 4. Dimension b does not include Dambar protrusion. Allowable Dambar protrusion shall be 0.08 mm total in excess of the b dimension at maximum material condition. Dambar cannot be located on the lower radius of the foot. Minimum space between protrusion and adjacent lead is 0.07 mm.
 5. Dimension D and E1 to be determined at Datum Plane H.

5/30/02



2325 Orchard Parkway
San Jose, CA 95131

TITLE

8A2, 8-lead, 4.4 mm Body, Plastic
Thin Shrink Small Outline Package (TSSOP)

DRAWING NO.

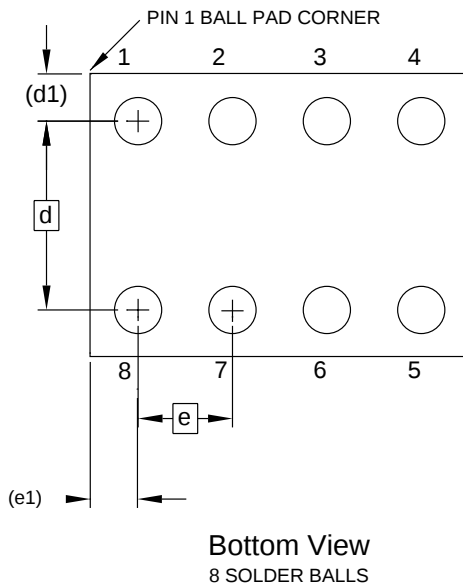
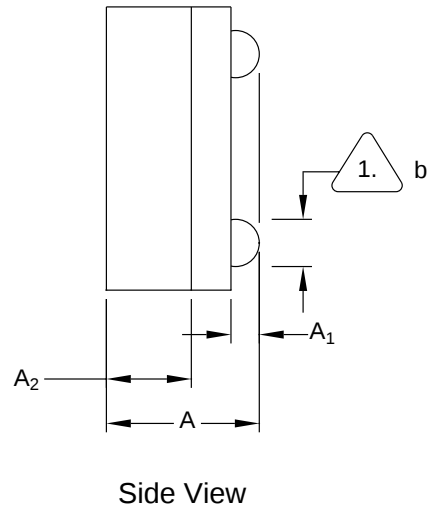
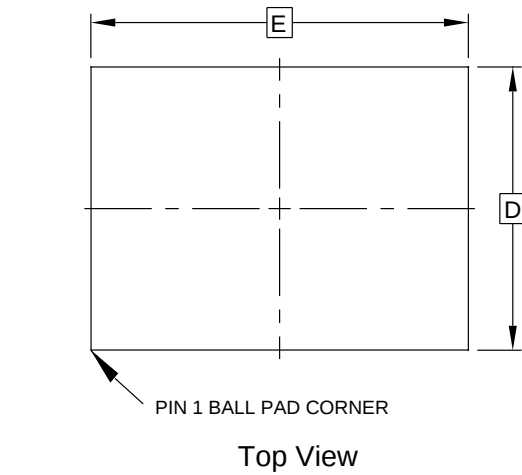
8A2

REV.

B



8U3-1 – dBGA2



COMMON DIMENSIONS
(Unit of Measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
A	0.71	0.81	0.91	
A1	0.10	0.15	0.20	
A2	0.40	0.45	0.50	
b	0.20	0.25	0.30	
D	1.50 BSC			
E	2.00 BSC			
e	0.50 BSC			
e1	0.25 REF			
d	1.00 BSC			
d1	0.25 REF			

1. Dimension 'b' is measured at the maximum solder ball diameter.

This drawing is for general information only.

6/24/03



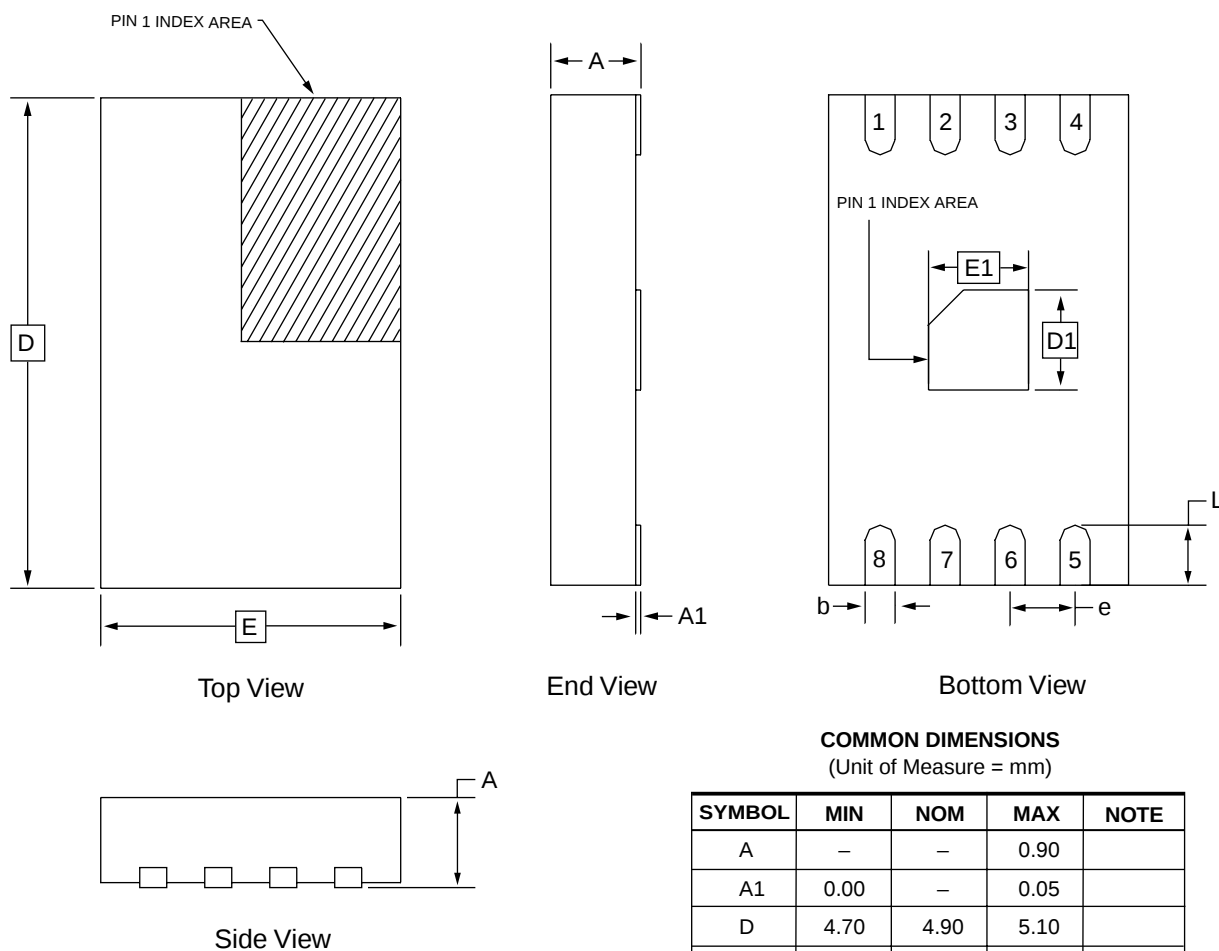
1150 E. Cheyenne Mtn. Blvd.
Colorado Springs, CO 80906

TITLE
8U3-1, 8-ball, 1.50 x 2.00 mm Body, 0.50 mm pitch,
Small Die Ball Grid Array Package (dBGA2)

DRAWING NO.
PO8U3-1

REV.
A

8Y1 – MAP



COMMON DIMENSIONS
(Unit of Measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
A	—	—	0.90	
A1	0.00	—	0.05	
D	4.70	4.90	5.10	
E	2.80	3.00	3.20	
D1	0.85	1.00	1.15	
E1	0.85	1.00	1.15	
b	0.25	0.30	0.35	
e	0.65 TYP			
L	0.50	0.60	0.70	

2/28/03



2325 Orchard Parkway
San Jose, CA 95131

TITLE

8Y1, 8-lead (4.90 x 3.00 mm Body) MSOP Array Package
(MAP) Y1

DRAWING NO.

8Y1

REV.

C





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